

Supplementary Information for

Quantifying the Damage Induced by XPS Depth Profiling of Organic Conjugated Polymers

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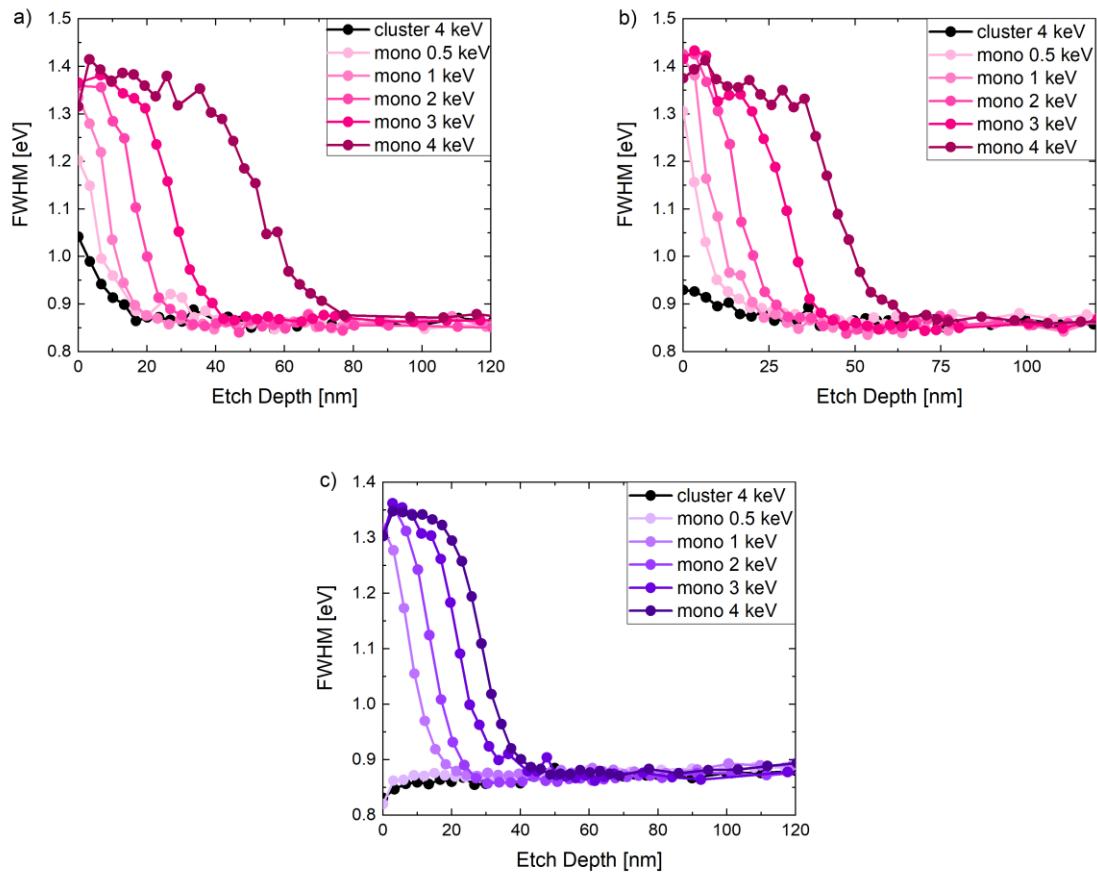


Figure S1. FWHM depth profile of the S2p peak of (a) annealed c-P3HT, (b) unannealed c-P3HT, and (c) unannealed a-P3HT.

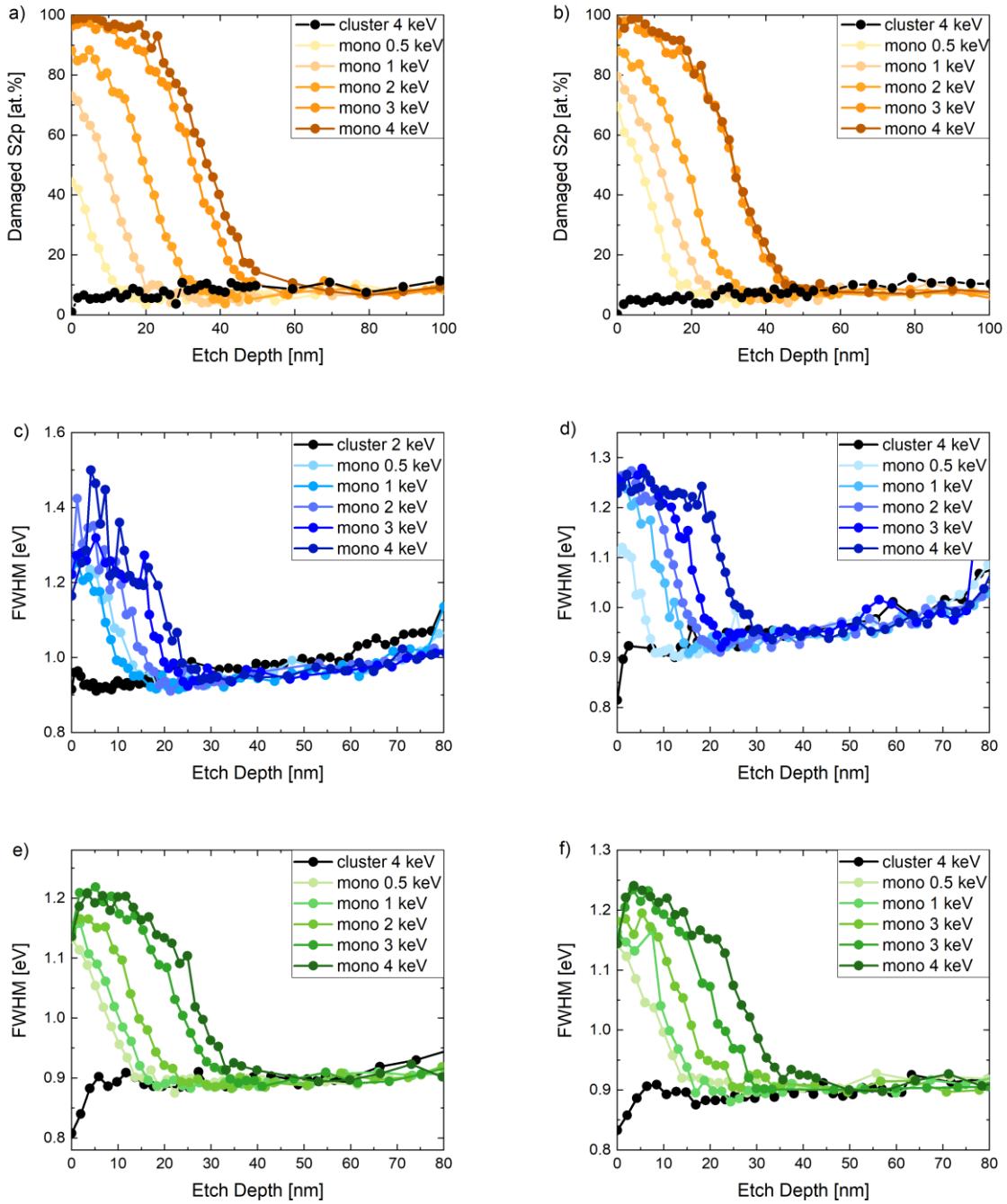


Figure S2. Depth profiles of the parameters indicating the mono damage. The percentage of damaged S_{2p} species in (a) annealed F8BT, and (b) unannealed F8BT. The S_{2p} FWHM of (c) annealed PTB7, (d) unannealed PTB7, (e) annealed PCE10, and (f) unannealed PCE10.

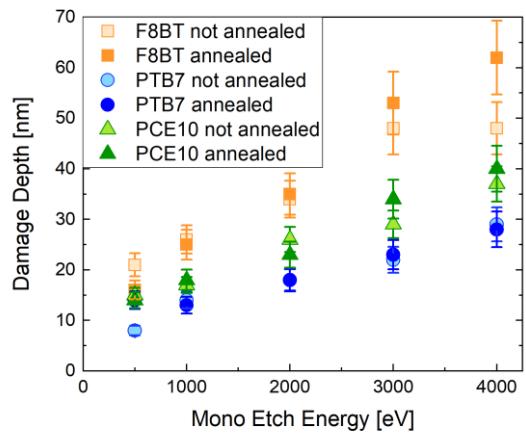


Figure S3. Damage depth over mono etch energy of annealed and not annealed films of F8BT, PTB7, and PCE10. The damage depth was read from the respective graphs in Figure S2.

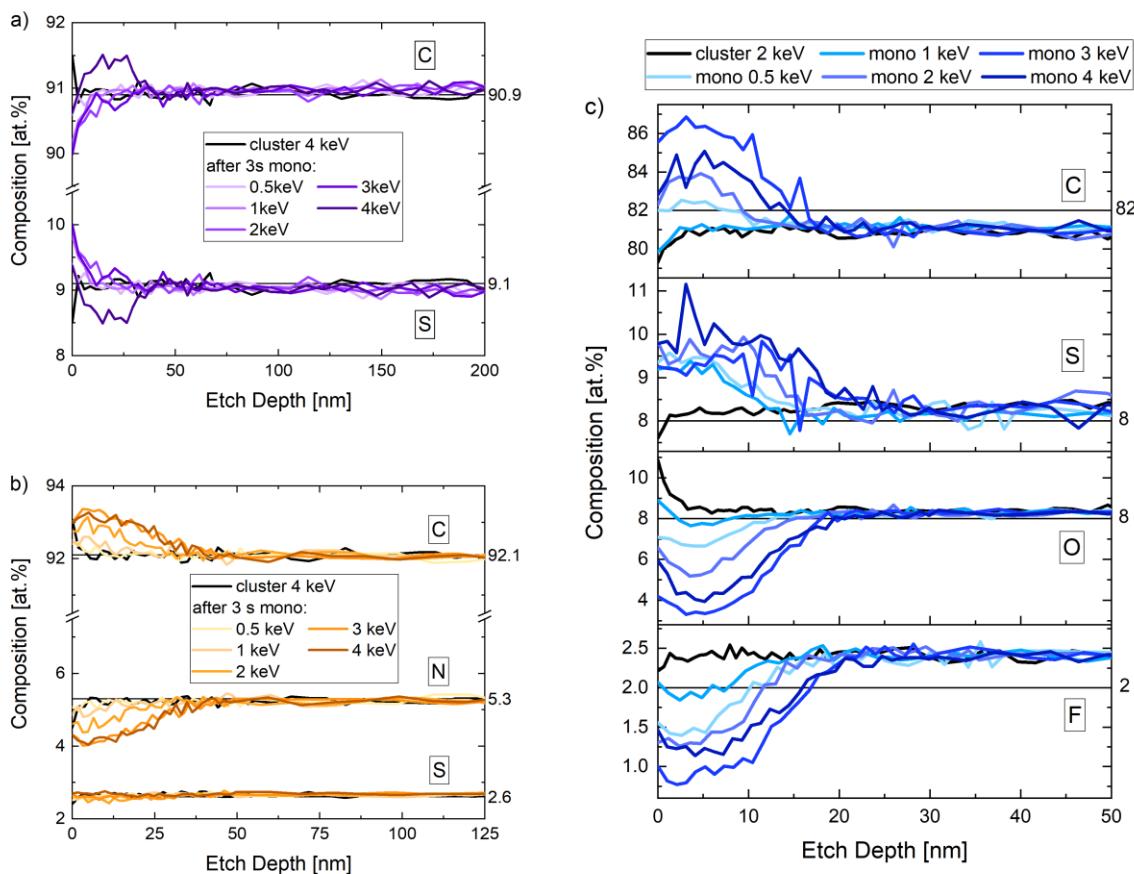


Figure S4. Compositional depth profiles of annealed films of (a) a-P3HT, (b) F8BT, and (c) PTB7. The theoretically expected percentages of each element are given on the right-hand side.

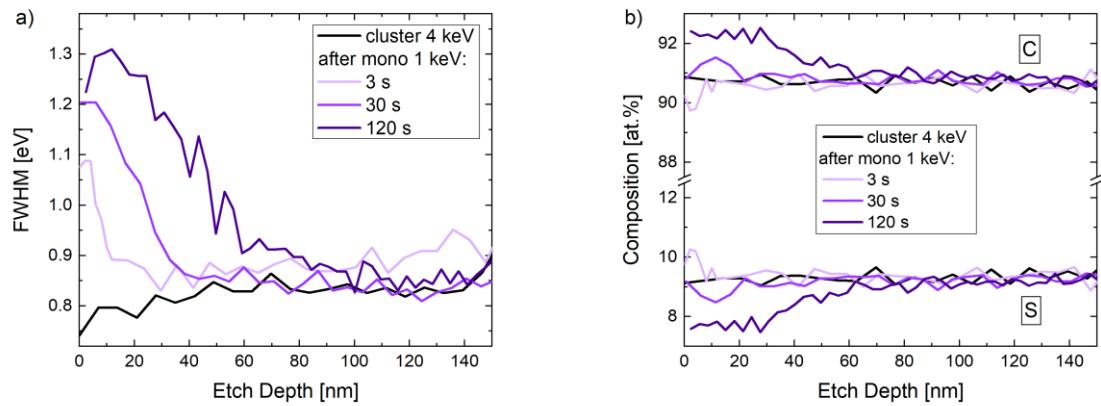


Figure S5. (a) S 2p FWHM and (b) compositional depth profiles of an annealed c-P3HT film after monoatomic etching (1 keV) of varying duration. The depth profiles have been corrected for the material removed by the monoatomic etching, which amounted to up to 2.4 nm after 120 s.